#### **BATTERY VOLTAGE**

# S63B1001

June 1997

## 1 Megabit (128K x8) CMOS Mask-Programmable ROM

#### **Features**

- Fast Read Access Time 70ns
- Low Power CMOS Operation
- 20μA max. Standby
- 15mA max. Active at 5MHz
- Wide Selection of JEDEC Standard Packages
  - 40-Lead 600-mil PDIP
  - 44-Pad PLCC
  - 40-Lead TSOP
  - 48-Lead TSOP
- 2.7V-3.6V Supply
- High Reliability CMOS Technology
- 2000V ESD Protection
- 200mA Latchup Immunity
- Two-line Control
- CMOS and TTL Compatible Inputs and Outputs
- Full Commercial and Industrial Temperature Ranges
- Designed for Battery Supply Operation

#### **Description**

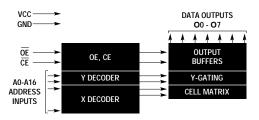
The S63B1001 is a low-power, high performance 1,048,576 bit Mask Programmable Read Only Memory (ROM) organized 128K x 8 bits. It requires only one power supply in normal operation. Any word can be accessed in less than 70ns, eliminating the need for speed reducing WAIT states on high-performance microprocessor systems.

The S63B1001 typically consumes 9mA. Standby mode supply current is typically less than  $10\mu A$ .

The S63B1001 comes in a choice of industry standard JEDEC-approved packages including: plastic PDIP, PLCC, and TSOP. The device features two-line control ( $\overline{\text{CE}}$ ,  $\overline{\text{OE}}$ ) to give designers the flexibility to prevent bus contention.

With high density 128K byte storage capability, the S63B1001 allows firmware to be stored reliably and to be accessed by the system without the delays of mass storage media. AMI's S63B1001 has additional features to ensure high quality and efficient production use.

#### **Block Diagram**



## **Absolute Maximum Ratings<sup>1</sup>**

Temperature Under Bias	-55°C to +125°C
Storage Temperature	-65°C to +150°C
Voltage on Any Pin with Respect to Ground	-2.0V to +6V <sup>2</sup>

NOTE: 1. Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent danger to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

 Minimum voltage is -0.6V DC which may undershoot to -2.0V for pulses less than 20ns. Maximum pin voltage is V<sub>CC</sub>+0.6V DC which may overshoot to +6.0V for pulses of less than 20ns.

#### **Pin Configurations**

PIN NAME	FUNCTION
A0-A16	Addresses
O0-O7	Outputs
CE	Chip Enable
ŌĒ	Output Enable
NC	No Connect

#### Pin Capacitance (f = 1 MHzT = 25°C)

	TYPICAL	MAXIMUM	UNITS	CONDITIONS
C <sub>IN</sub>	4	8	pF	$V_{IN} = 0V$
C <sub>OUT</sub>	8	12	pF	V <sub>OUT</sub> = 0V

NOTE: Typical values for nominal supply voltage. This parameter is only sampled and is not 100% tested.

# S63B1001



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## **Operating Modes**

MODE/PIN	CE	ŌĒ	Ai	V <sub>CC</sub>	OUTPUTS
Read	V <sub>IL</sub>	V <sub>IL</sub>	Ai	V <sub>CC</sub>	D <sub>OUT</sub>
Output Disable	X	V <sub>IH</sub>	X	V <sub>CC</sub>	High Z
Standby	V <sub>IH</sub>	Х	Х	V <sub>CC</sub>	High Z

## **DC and AC Operating Conditions**

	S63B1001									
-70 -90 -120										
Operating Temperature	Commercial	0°C - 70°C	0°C - 70°C	0°C - 70°C						
	Industrial	-40°C - 85°C	-40°C - 85°C	-40°C - 85°C						
V <sub>dd</sub> Power Supply	•	2.7V - 3.6V	2.7V - 3.6V	2.7V - 3.6V						

## **DC and Operating Characteristics**

## 2.7V to 3.6V

SYMBOL	PARAMETER	CONDITION	APP.	MIN	MAX	UNITS
I <sub>LI</sub>	Input Load Current	$V_{IN} = 0V \text{ to } V_{CC}$	Com., Ind.		±1	μΑ
I <sub>LO</sub>	Output Leakage Current	V <sub>OUT</sub> = 0V to V <sub>CC</sub>	Com., Ind.		±5	μΑ
I <sub>SB</sub>	V <sub>CC</sub> Standby Current	$\overline{CE} = V_{CC} \pm 0.3V$			20	μΑ
I	V <sub>CC</sub> Active Current	f = 5MHz, I <sub>OUT</sub> = 0mA,	Com.		15	mA
Icc	ACC Verive Carretic	$\overline{\text{CE}} = V_{\text{IL}}, V_{\text{CC}} = 3.6V$	Ind.		20	mA
V	Input Low Voltage	V <sub>CC</sub> = 3.0V to 3.6V			0.8	V
V <sub>IL</sub> I	input Low voltage	V <sub>CC</sub> = 2.7V to 3.6V			0.2 x V <sub>CC</sub>	V
V	Input High Voltage	V <sub>CC</sub> = 3.0V to 3.6V		2.2		V
V <sub>IH</sub>	Input High Voltage	V <sub>CC</sub> = 2.7V to 3.6V		0.7 x V <sub>CC</sub>		V
		2mA			0.4	V
V <sub>OL</sub>	Output Low Voltage	100μΑ			0.2	V
		20μΑ			0.1	V
		-1mA		2.2		V
V <sub>OH</sub>	Output High Voltage	-100μΑ		V <sub>CC</sub> - 0.2		V
		-20μΑ		V <sub>CC</sub> - 0.1		V



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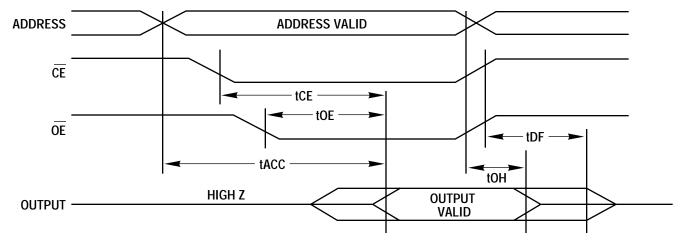
# 1 Megabit (128K x8) CMOS Mask-Programmable ROM

## **AC Characteristics for Read Operations**

## 2.7V - 3.6V

	S63B1001											
SYMBOL	PARAMETER	CONDITION	-70		-9	90	-120					
STIVIDUL	PARAWETER	CONDITION	Min.	Max.	Min.	Max.	Min.	Max.				
t <sub>ACC</sub> <sup>3</sup>	Address to Output Delay		70ns		90ns		120ns					
t <sub>CE</sub> <sup>2</sup>	CE to Output Delay	OE=V <sub>IL</sub>		70ns		90ns		120ns				
t <sub>OE</sub> <sup>2,3</sup>	OE to Output Delay	CE=V <sub>IL</sub>		30ns		35ns		35ns				
t <sub>DF</sub> <sup>4,5</sup>	OE or CE High to Output Float			25ns		25ns		30ns				
t <sub>OH</sub>	Output Hold from Addresses, Coccurred first	E or OE whichever	0ns		0ns		0ns					

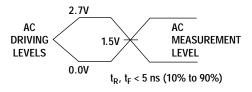
## **AC Waveforms<sup>1</sup>**



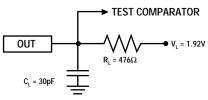
Notes:1. Timing measurement references are 1.5V. Input AC driving levels are 0V and 2.7V.

- 2.  $\overline{\text{OE}}$  may be delayed up to  $t_{\text{CE}}$ - $t_{\text{OE}}$  after the falling edge of  $\overline{\text{CE}}$  without impact on  $t_{\text{CE}}$ .
- 3.  $\overline{\text{OE}}$  may be delayed up to  $t_{\text{ACC}}$ - $t_{\text{OE}}$  after the address is valid without impact on  $t_{\text{ACC}}$ .
- 4. This parameter is only sampled and is not 100% tested.
- 5. Output float is defined as the point when data is no longer driven.

## **Input Test Waveforms and Measurement Levels**



## **Output Test Load**





#### **Standard Products**

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## 32-Pin PDIP Specifications

#### **Description**

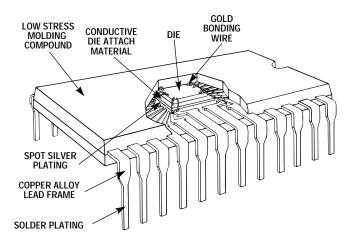
The Plastic Dual-In-Line Package (PDIP) meets widely accepted industry standard for MOS/VLSI applications. The package consists of a plastic body, transfer-molded around the leadframe and die. The leadframe is copper alloy, with external pins solder plated.

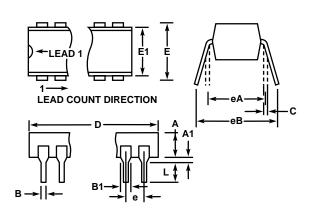
Internally, there is  $125\mu$  inch silver spot plating on the die attach pad and on each bonding fingertip. These fingers are electrically connected to the die by thermosonic gold ball bonding techniques.

## **Pin Configuration**

NC 1	- <del></del>	¬¬ vcc
NC 1 1 A16 2 3 A12 3 4 A7 5 5 A6 6 7 A4 4 7 8 A3 7 7 10 A1 10 A1 11 A0 11 O0 11 GND 16 GND 16	3.	
A15 🗖 3		рЫрмс
A12 🗖 4	30 24 25 20 29 24 25 22 27 20 19	9 🗖 A14
A7 🕇 5	28	B 🔁 A13
A6 <b>戊</b> 6	2	7 🗖 A8
A5 🗖 7	20	5 🗖 A9
A4 🗖 8	2!	5 🗀 A11
A3 🗖 9	24	4 <b>)</b> 0E
A2 🗖 10	23	3 🗖 A10
A1 🗖 11	2	2 📛 Œ
A0 🗖 12	2	1 🔰 07
<b>O</b> 0 🗖 13	20	<b>)   0</b> 6
01 🗖 14	19	9 <b>&gt; 0</b> 5
O2 5 15 GND 16	18	504
GND 🗖 16	1	7 <b>5 0</b> 3

#### **Package Description and Outline Dimensions**





#### **PDIP Specifications**

	SYMBOL													
	Α	<b>A</b> 1	В	B1	С	D	E	E1	е	eA	eВ	L	B2	S
MAX	0.180	-	0.020	0.055	0.012	1.655	0.625	0.550	0.100	-	0.686	0.135	-	-
MIN	-	0.015	0.016	0.045	0.008	1.645	0.600	0.530	TYP	0.580	-	0.125	-	-

NOTE: 1. All measurements in inches.

<sup>2.</sup> Data is subject to change. Contact the factory for most current specifications.



## 1 Megabit (128K x8) CMOS Mask-Programmable ROM

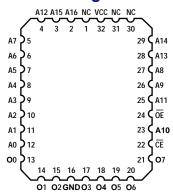
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## **32-Pin PLCC Specifications**

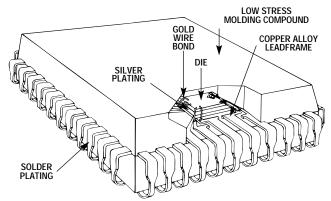
#### **Description**

The PLCC is transfer molded and thermosonic wire bonded. Die is mounted on a copper alloy leadframe and external leads are solder plated to provide improved solderability.

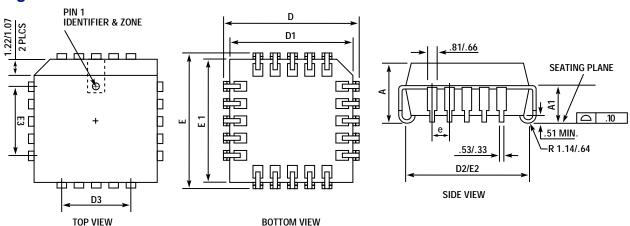
#### **Pin Configuration**



## **Package Description**



## **Package Outline Dimensions**



## **PDIP Specifications**

	SYMBOL												
	Α	A1	D1	D2	D3	E1	E2	E3	е	D	E		
MAX	3.56	2.41	11.51	10.92	7.62	14.05	13.46	10.16	1.27	12.57	15.11		
MIN	2.45	1.52	11.35	9.91	BSC	13.89	12.45	BSC	BSC	12.32	14.86		

NOTE: 1. All measurements in millimeters

<sup>2.</sup> Data is subject to change. Contact the factory for most current specifications



#### **Standard Products**

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## 1 Megabit (128K x8) CMOS Mask-Programmable ROM

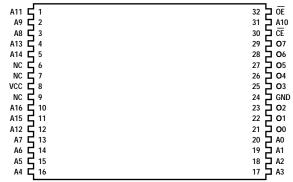
## 32-Pin TSOP Specifications

#### **Description**

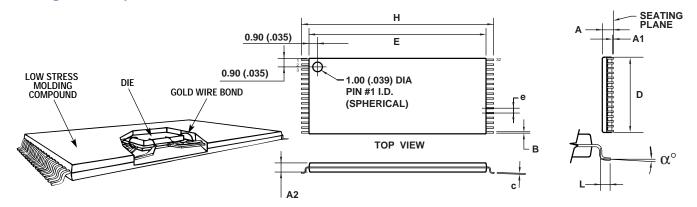
The Type I Thin Small Outline Package (TSOP) is a thin, ends only package. This package is constructed using the latest low stress molding compounds and bonding technology to provide a package with total body thickness of less than 1.90mm.

This package is popular for ROM applications in memory cards and other thin card applications.

## **Pin Configuration**



#### **Package Description and Outline Dimensions**



#### **TSOP Specifications**

	SYMBOL												
	Α	A1	A2	В	D	E	Н	е	С	L	α°		
MAX	1.20	0.15	1.05	0.25	8.20	18.50	20.20	0.50	0.20	0.60	5		
MIN	-	0.0	0.95	0.15	7.80	18.30	19.80	BSC	0.10	0.40	0		

NOTE: 1. All measurements in millimeters.

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